
Errata

Erratum: Phase transitions in InSb at pressures up to 5 GPa
[Phys. Rev. B 47, 35 (1993)]

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Some of the features in the two-dimensional images published as part of this paper were not visible. Those images are republished here.

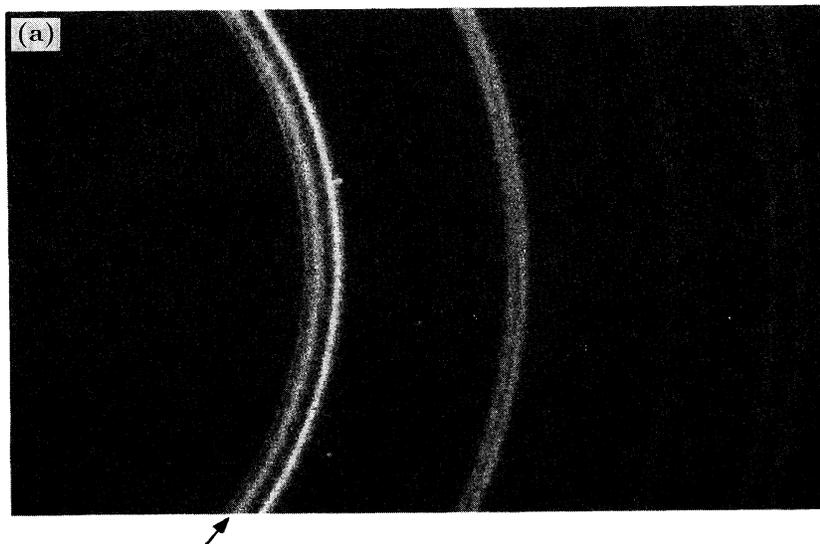


FIG. 3. (a) A pattern recorded from a mixture of InSb *P2* and *P3* at, or slightly above, the pressure in Fig. 2. The arrow marks the first line of one phase (*P3*). The adjacent broader lines are the first two of the second phase (*P2*). $\lambda=0.4442 \text{ \AA}$. Exposure time = 10 min. Sample-to-plate distance = 350 mm. (b) The corresponding integrated profile. The asterisks mark the sharp-peaked features of *P3*. The inset displays the first three peaks on the same 2θ scale as in the inset of Fig. 2.

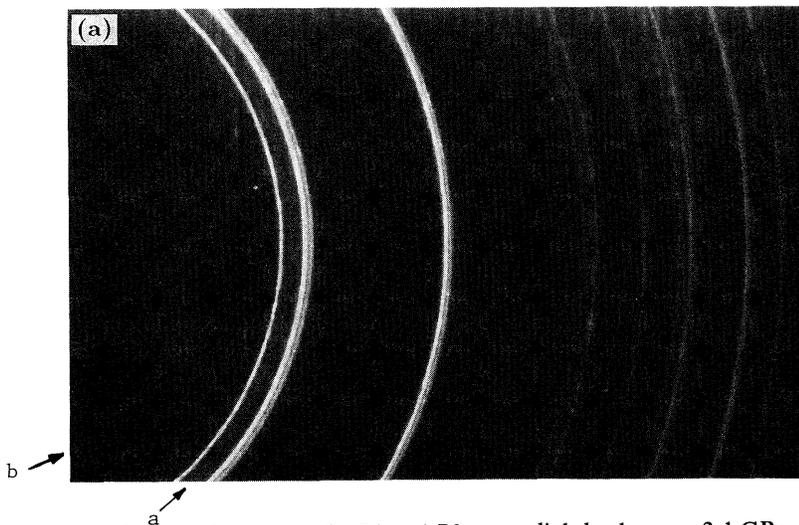


FIG. 4. (a) A pattern recorded from a mixture of InSb *P2* and *P3* at, or slightly above, $\sim 2.1 \text{ GPa}$. The lowest-angle strong line of *P2* is labeled "a" and the very weak low-angle line of *P3* is labeled "b." $\lambda=0.4446 \text{ \AA}$. Exposure time = 14 min. Sample-to-plate distance = 250 mm. (b) The corresponding integrated profile. The arrows below the profile mark the two nonoverlapped *P2* lines (the one at $2\theta \sim 9^\circ$ is marked "a" in the 2D pattern). The features marked Δ and $*$ [inset (i)] are discussed in the text. Inset (ii) shows the very weak low-angle line of *P3* (marked "b" in the 2D pattern) recorded with an incident energy of 25.83 keV, far (*f*) from the In *K* edge (as in the main profile), and at 27.886 keV near (*n*) the In *K* edge (at 27.925 keV). Inset (iii) shows the cubic (200) reflection recorded with the same two incident x-ray energies as for inset (ii).

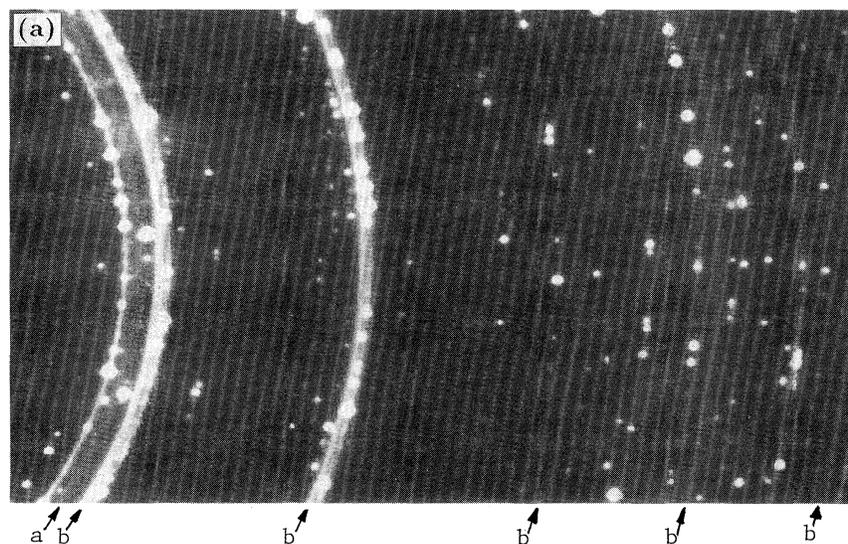


FIG. 6 (a) A pattern recorded from a sample of InSb *P3* partly transformed to *P4* just above 2.1 GPa. Some *P2* is also still present, as shown by the line labeled “a.” The *P3* lines labeled “b” are not overlapped by any *P4* lines, and hence are free from spots. $\lambda=0.4446 \text{ \AA}$. Exposure=10 min. Sample-to-plate distance=250 mm. (b) The corresponding integrated profile. Asterisks mark the strongest of the nonoverlapped *P3* lines, labeled “b” in (a). The low-angle weak line of *P3* is enlarged in inset (i), with a weak *P4* line alongside. Inset (ii) shows the part of the profile below $2\theta=15^\circ$, with the best-fitting calculated *P3* profile subtracted to reveal the main *P4* lines.

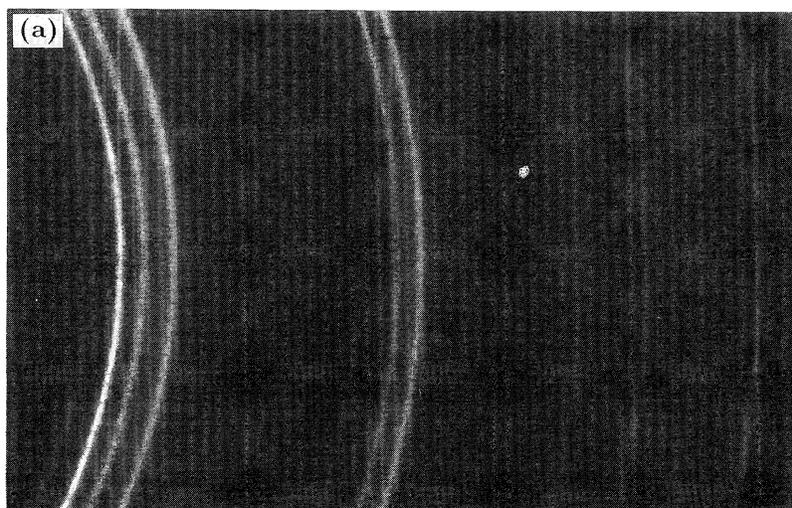


FIG. 8 (a) A pattern recorded from InSb *P4* at ~ 3 GPa, just above the transition directly from the cubic phase. $\lambda=0.4446 \text{ \AA}$. Exposure time=42 min. Sample-to-plate distance=250 mm. (b) The corresponding integrated profile. The insets show parts of the profile enlarged, as indicated. The arrow below the main profile indicates a weak non-*P4* line. The marked features in the insets are discussed in the text.

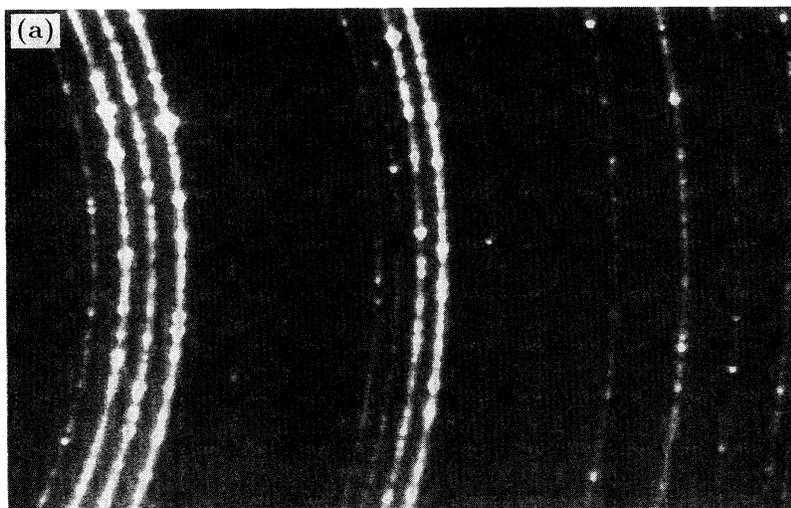


FIG. 9 (a) A pattern recorded from InSb *P4* at ~ 2.5 GPa and 100°C . $\lambda = 0.4642 \text{ \AA}$. Exposure time = 146 min. Sample-to-plate distance = 250 mm. (b) The corresponding integrated profile. Inset (i) shows a weak low-angle line recorded with an incident x-ray energy of 26.709 keV, far (*f*) from the In *K* edge (as in the main profile), and at 27.886 keV, near (*n*) in the In *K* edge at (27.925 keV). The enlargement in inset (ii) reveals many weak superlattice reflections, marked Δ . Two of these are enlarged further in inset (iii), recorded far from and near the In *K* edge as in (i).

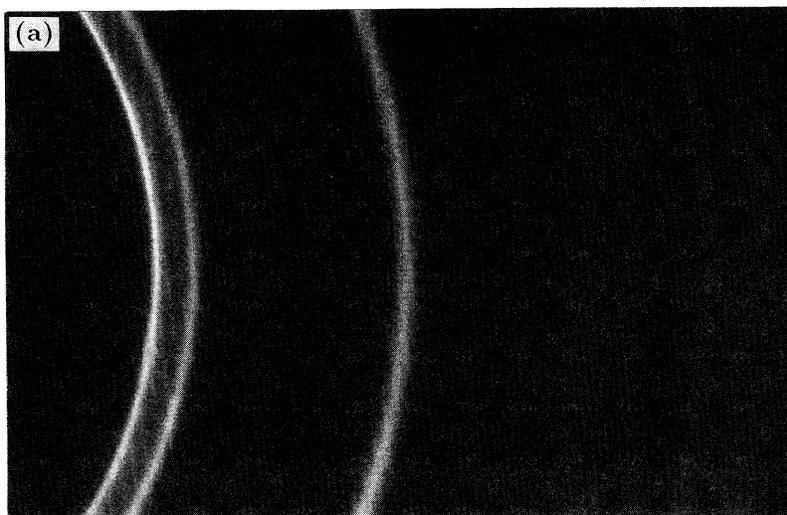


FIG. 12. (a) A pattern recorded from InSb at about 2.3 GPa after passing rapidly through the transition. $\lambda = 0.4442 \text{ \AA}$. Exposure time = 51 min. Sample-to-plate distance = 200 mm. (b) The corresponding integrated profile, and its subsequent evolution over a period of 2 days. The triangles under the initial profile show the positions of the principal β -tin lines. The one marked by a solid triangle at $2\theta \sim 22^\circ$ is the nonoverlapping *P2* line indicated at the same position in Fig. 4(b). The weak low-angle is enlarged in the inset.

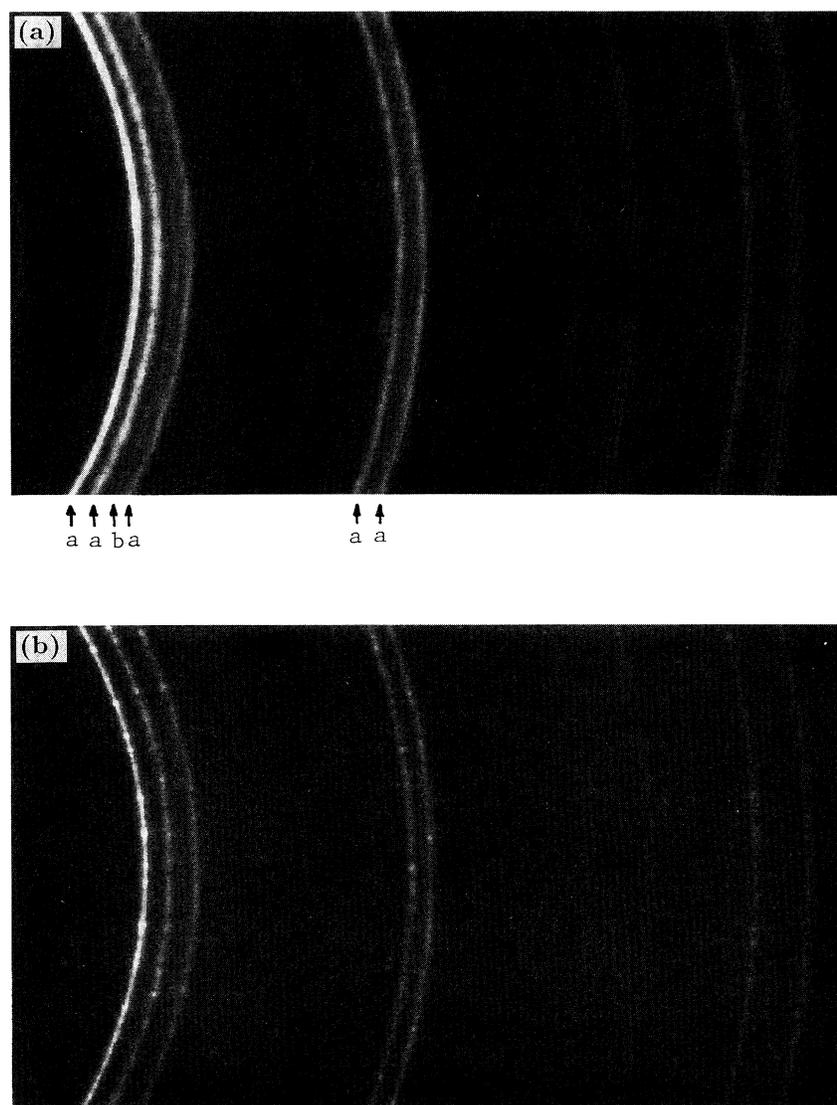


FIG. 15. (a) A mixed $P3$ - $P4$ pattern recorded from InSb after passing through the transition at ~ 3.0 GPa. The strongest $P4$ lines are labeled "a," and the single visible $P3$ line is labeled "b." $\lambda = 0.4446$ Å. Exposure time = 26 min. Sample-to-plate distance = 250 mm. (b) A pattern recorded from the same sample 15 h later, after $P3$ has recrystallized to $P4$. $\lambda = 0.4446$ Å. Exposure time = 42 min. Sample-to-plate distance = 250 mm.

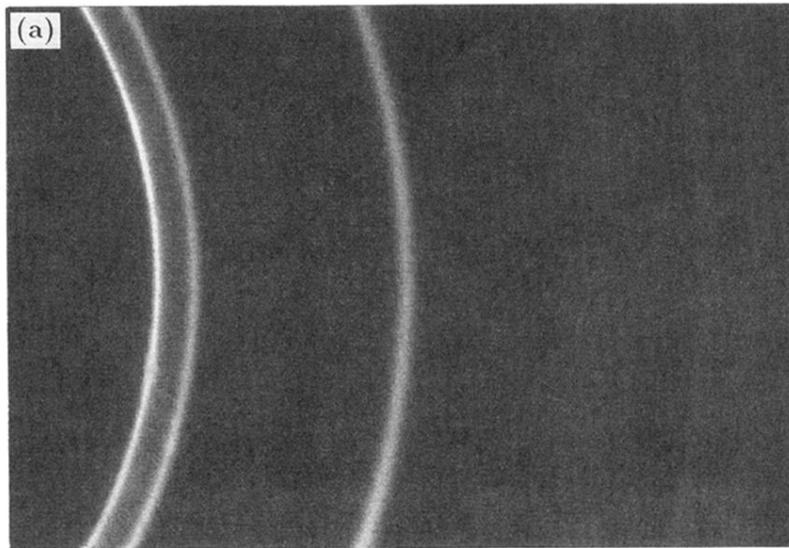


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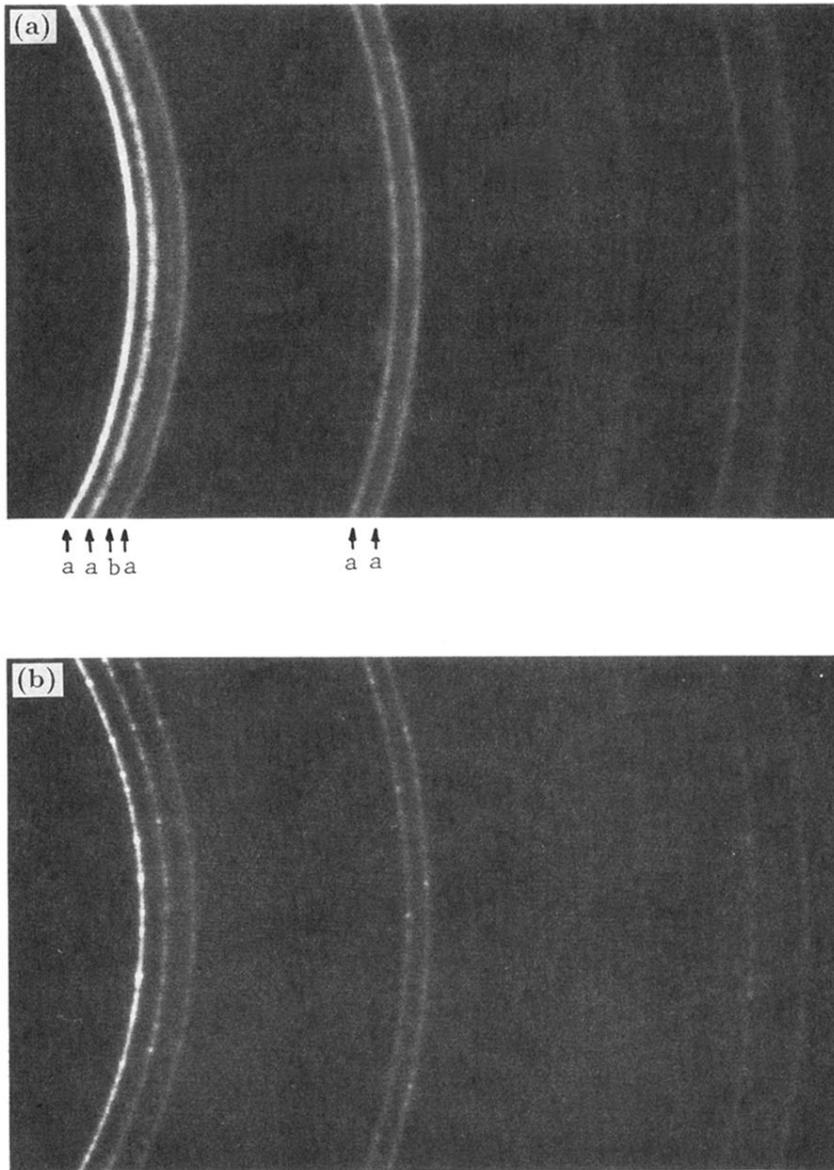


FIG. 15. (a) A mixed $P3$ - $P4$ pattern recorded from InSb after passing through the transition at ~ 3.0 GPa. The strongest $P4$ lines are labeled "a," and the single visible $P3$ line is labeled "b." $\lambda=0.4446$ Å. Exposure time=26 min. Sample-to-plate distance=250 mm. (b) A pattern recorded from the same sample 15 h later, after $P3$ has recrystallized to $P4$. $\lambda=0.4446$ Å. Exposure time=42 min. Sample-to-plate distance=250 mm.

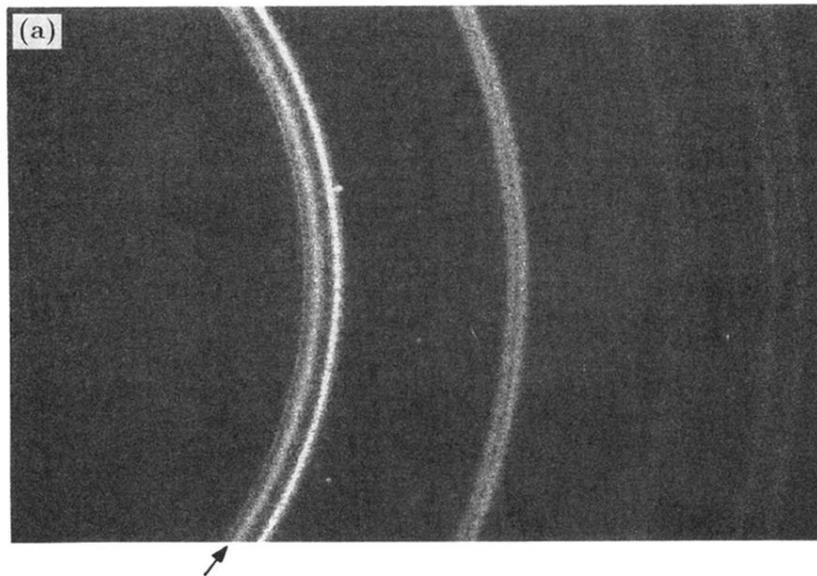


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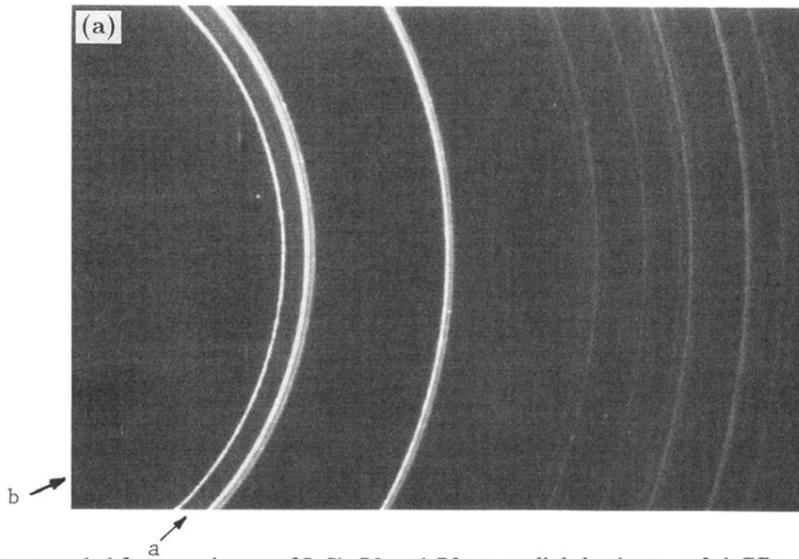


FIG. 4. (a) A pattern recorded from a mixture of InSb $P2$ and $P3$ at, or slightly above, ~ 2.1 GPa. The lowest-angle strong line of $P2$ is labeled “a” and the very weak low-angle line of $P3$ is labeled “b.” $\lambda = 0.4446 \text{ \AA}$. Exposure time = 14 min. Sample-to-plate distance = 250 mm. (b) The corresponding integrated profile. The arrows below the profile mark the two nonoverlapped $P2$ lines (the one at $2\theta \sim 9^\circ$ is marked “a” in the 2D pattern). The features marked Δ and $*$ [inset (i)] are discussed in the text. Inset (ii) shows the very weak low-angle line of $P3$ (marked “b” in the 2D pattern) recorded with an incident energy of 25.83 keV, far (f) from the In K edge (as in the main profile), and at 27.886 keV near (n) the In K edge (at 27.925 keV). Inset (iii) shows the cubic (200) reflection recorded with the same two incident x-ray energies as for inset (ii).

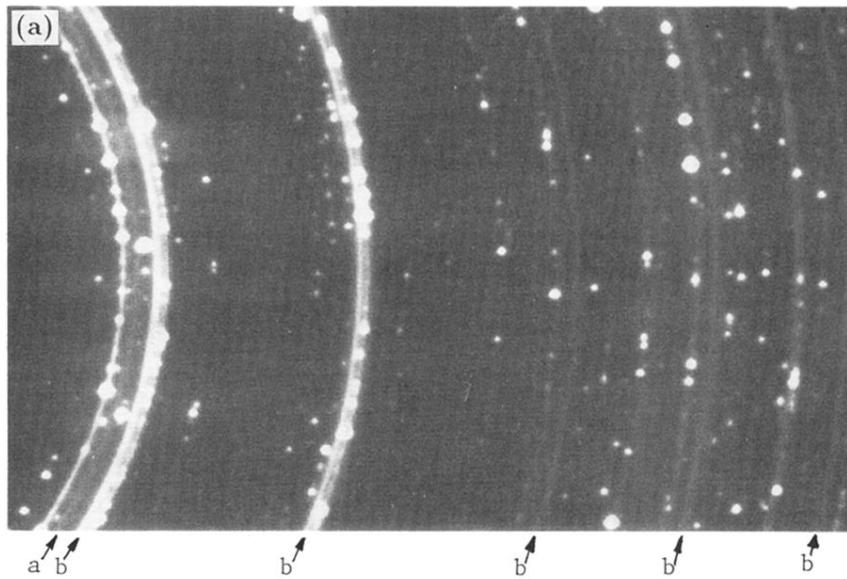


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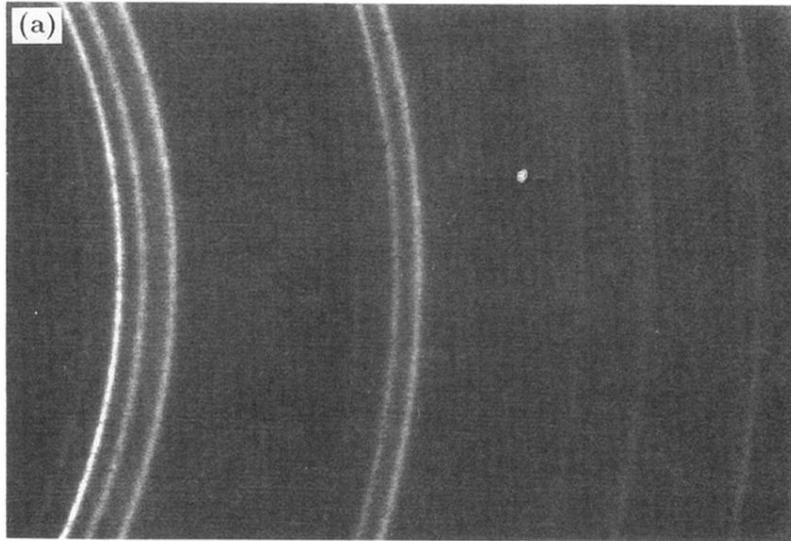


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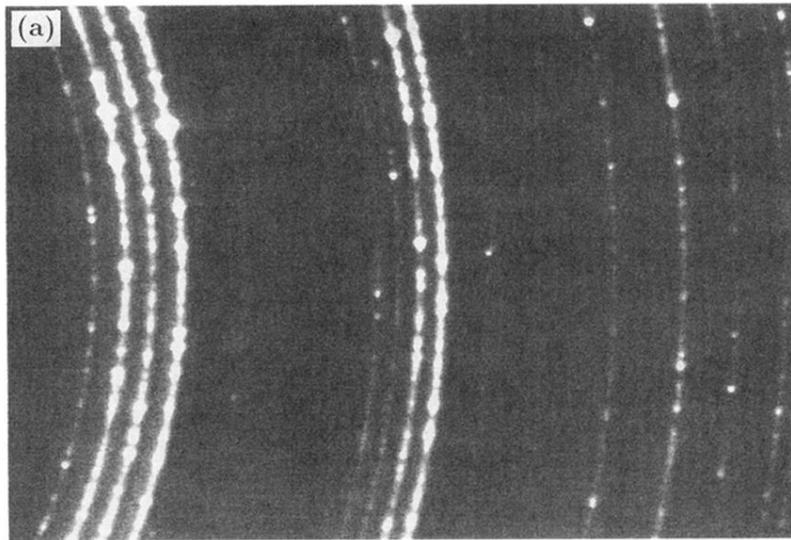


FIG. 9 (a) A pattern recorded from InSb *P4* at ~ 2.5 GPa and 100°C . $\lambda = 0.4642 \text{ \AA}$. Exposure time = 146 min. Sample-to-plate distance = 250 mm. (b) The corresponding integrated profile. Inset (i) shows a weak low-angle line recorded with an incident x-ray energy of 26.709 keV, far (*f*) from the In *K* edge (as in the main profile), and at 27.886 keV, near (*n*) in the In *K* edge at (27.925 keV). The enlargement in inset (ii) reveals many weak superlattice reflections, marked Δ . Two of these are enlarged further in inset (iii), recorded far from and near the In *K* edge as in (i).